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COMPLEMENTARY 60V NPN/PNP MEDIUM POWER TRANSISTORS IN SOT26

Features

NPN Transistor

- BV_{CEO} > 60V
- I_C = 1A Continuous Collector Current
- Low Saturation Voltage (500mV max @ 1A)
- h_{FE} characterised up to 2A
- R_{SAT} = 210mΩ @1A for a Low Equivalent On-Resistance

PNP Transistor

- BV_{CEO} > -60V
- I_C = -1A Continuous Collector Current
- Low Saturation Voltage (-600mV max @ -1A)
- hFE characterised up to 2A

 $R_{SAT} = 355 m\Omega$ @1A for a Low Equivalent On-Resistance

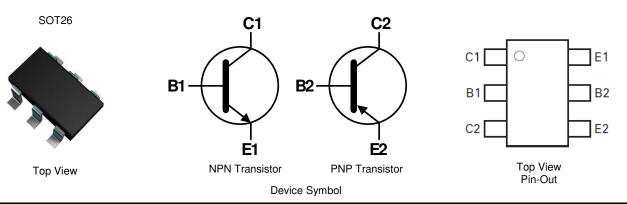
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT26
- Case Material: Molded Plastic, "Green" Molding Compound;
 UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020 Terminals: Finish – Matte Tin Plated Leads;
- Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.015 grams (Approximate)

Applications

- MOSFET Gate Driver
- Low Power Motor Drive
- Low Power DC-DC Converters



Ordering Information (Note 4)

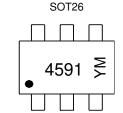
Ī	Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
	ZXTD4591E6TA	AEC-Q101	4591	7	8	3,000

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

Document Number: DS33652 Rev: 2 - 2



4591 = Product Type Marking Code YM = Date Code Marking

Y or \overline{Y} = Year (ex: C = 2015)

M or \overline{M} = Month (ex: 9 = September)

Date Code Kev

Year	2015	2	016	2017	2018	2019	2020	202	1 20	22 2	2023	2024	2025
Code	С		D	Е	F	G	Н		,	J	K	L	М
Month	1	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code		1	2	3	4	5	6	7	8	9	0	N	D

www.diodes.com



NPN - Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	80	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	V _{EBO}	7	V
Peak Pulse Current	I _{CM}	2	Α
Continuous Collector Current	Ic	1	Α
Base Current	Ι _Β	500	mA

PNP - Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-80	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V_{EBO}	-7	V
Peak Pulse Current	Ісм	-2	Α
Continuous Collector Current	Ic	-1	Α
Base Current	I _B	-500	mA

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 6)		1.1 8.8	W
Linear Derating Factor	(Note 7)	P _D	1.7 13.6	mW/°C
Thermal Resistance, Junction to Ambient	(Note 6) (Note 7)	R ₀ JA	113 73	°C/W
Thermal Resistance, Junction To Lead	$R_{\theta JL}$	74	°C/W	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

ESD Ratings (Note 9)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	٧	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

^{6.} For a device mounted with the collector lead on 25mm x 25mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; the device is measured under still air conditions whilst operating in a steady-state. Two active dice running at equal power with heatsink split 50% to each collector.

7. Same as Note 6, except the device is measured at t < 5 seconds.

^{8.} Thermal resistance from junction to solder-point (at the end of the collector lead).

9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



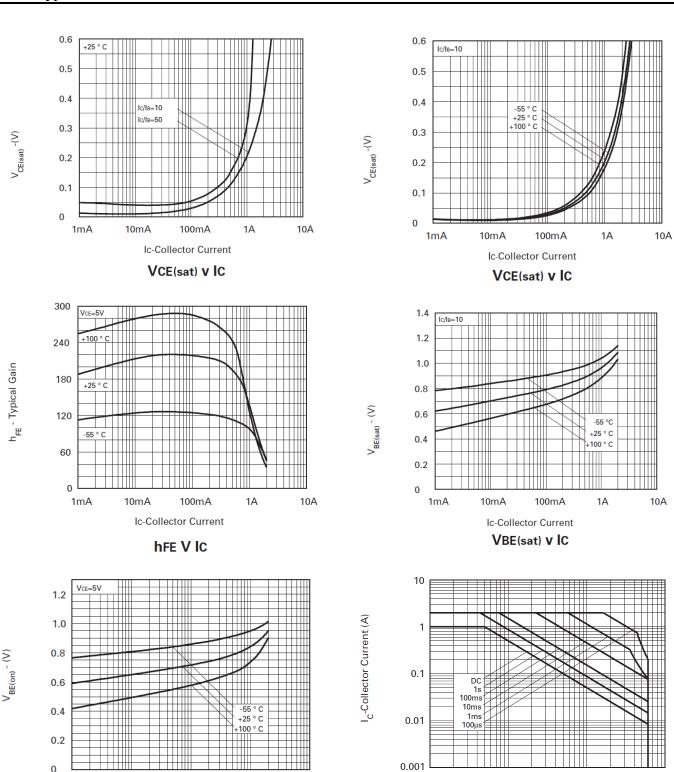
NPN - Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS							
Collector-Base Breakdown Voltage	BV_{CBO}	80	_		٧	$I_C = 100\mu A, I_E = 0$	
Collector-Emitter Breakdown Voltage (Note 10)	BV_CEO	60	_		٧	$I_C = 10 \text{mA}, I_B = 0$	
Emitter-Base Breakdown Voltage	BV_{EBO}	7	_		V	$I_E = 100 \mu A, I_C = 0$	
Collector Cut-Off Current	I _{CBO}	_	_	100	nA	$V_{CB} = 60V$	
Emitter Cut-Off Current	I _{EBO}	_	_	100	nA	V _{EB} =5.6	
Emitter Cut-Off Current	I _{CES}	_	_	100	nA	$V_{CE} = 60V$	
ON CHARACTERISTICS (Note 10)							
DC Current Gain	h _{FE}	100 100 80 30		300 —	_	$\begin{split} I_{C} &= 1 m A, \ V_{CE} = 5 V \\ I_{C} &= 500 m A, \ V_{CE} = 5 V \\ I_{C} &= 1 A, \ V_{CE} = 5 V \\ I_{C} &= 2 A, \ V_{CE} = 5 V \end{split}$	
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_		0.25 0.5	> >	$I_C = 500$ mA, $I_B = 50$ mA $I_C = 1$ A, $I_B = 100$ mA	
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	_	1.1	V	$I_C = 1A$, $I_B = 100mA$	
Base-Emitter Turn-On Voltage	$V_{BE(on)}$	_	_	1.0	V	$I_C = 1, V_{CE} = 5V$	
SMALL SIGNAL CHARACTERISTICS							
Output Capacitance	C_{obo}		_	10	рF	$V_{CB} = 10V, f = 1.0MHz$	
Current Gain Bandwidth Product	f _T	180	_		MHz	$I_C = 50 \text{mA}, V_{CE} = 10 \text{V}$ f = 100MHz	

Note: 10. Measured under pulsed conditions. Pulse width \leq 300 μ s. Duty cycle \leq 2%.



NPN - Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)



0.1

1mA

10mA

100mA

Ic-Collector Current

1A

0

10A

100

10

VcE - Collector Emitter Voltage (V)



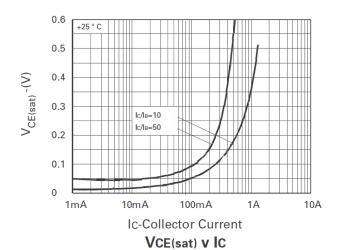
PNP - Electrical Characteristics (@TA = +25°C, unless otherwise specified.)

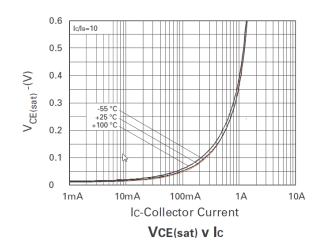
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition		
OFF CHARACTERISTICS								
Collector-Base Breakdown Voltage	BV_CBO	-80	_	_	V	$I_C = -100\mu A, I_E = 0$		
Collector-Emitter Breakdown Voltage (Note 10)	BV_CEO	-60	_	_	V	$I_C = -10 \text{mA}, I_B = 0$		
Emitter-Base Breakdown Voltage	BV _{EBO}	-7	_	_	٧	$I_E = -100\mu A, I_C = 0$		
Collector Cut-Off Current	I _{CBO}	_		-100	nA	$V_{CB} = -60V$		
Emitter Cut-Off Current	I _{EBO}	_		-100	nA	$V_{EB} = -5.6V$		
Emitter Cut-Off Current	I _{CES}	_	_	-100	nA	$V_{CE} = -60V$		
ON CHARACTERISTICS (Note 10)								
DC Current Gain	h _{FE}	100 100 80 15		300 —	_	$\begin{split} I_{C} &= -1 m A, \ V_{CE} = -5 V \\ I_{C} &= -500 m A, \ V_{CE} = -5 V \\ I_{C} &= -1 A, \ V_{CE} = -5 V \\ I_{C} &= -2 A, \ V_{CE} = -5 V \end{split}$		
Collector-Emitter Saturation Voltage	V _{CE(sat)}	_		-0.3 -0.6	> >	$I_C = -500 \text{mA}, I_B = -50 \text{mA}$ $I_C = -1 \text{A}, I_B = -100 \text{mA}$		
Base-Emitter Saturation Voltage	V _{BE(sat)}	_	_	-1.2	V	$I_C = -1A$, $I_B = -100mA$		
Base-Emitter Turn-On Voltage	$V_{BE(on)}$	_	_	-1.0	V	$I_C = -1A$, $V_{CE} = -5V$		
SMALL SIGNAL CHARACTERISTICS	SMALL SIGNAL CHARACTERISTICS							
Output Capacitance	C_{obo}		_	10	рF	$V_{CB} = -10V, f = 1.0MHz$		
Current Gain Bandwidth Product	f _T	150	_	_	MHz	$I_C = -50 \text{mA}, V_{CE} = -10 \text{V}$ f = 100MHz		

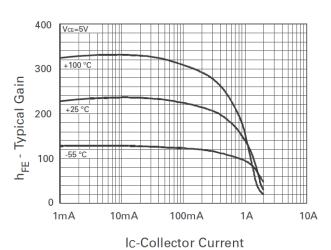
Note: 10. Measured under pulsed conditions. Pulse width $\leq 300 \mu s$. Duty cycle $\leq 2\%$.

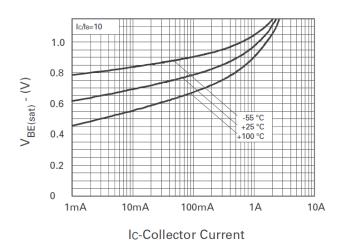


PNP - Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



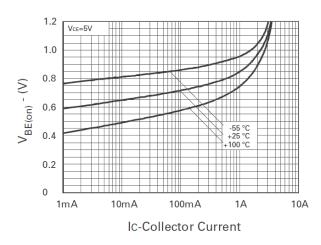


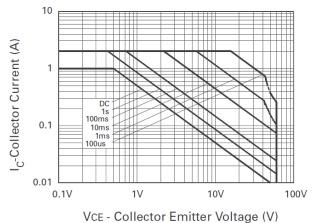




hFE V IC

VBE(sat) v Ic





VBE(on) v IC

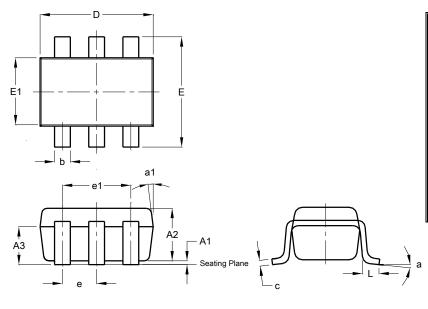
E Concetor Ennitter Voltage (V

Safe Operating Area



Package Outline Dimensions

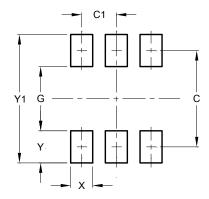
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



	SC	OT26					
Dim	Min	Max	Тур				
A 1	0.013	0.10	0.05				
A2	1.00	1.30	1.10				
A 3	0.70	0.80	0.75				
b	0.35	0.50	0.38				
C	0.10	0.20	0.15				
D	2.90	3.10	3.00				
е	-	-	0.95				
e1	-	-	1.90				
Е	2.70	3.00	2.80				
E1	1.50	1.70	1.60				
L	0.35	0.55	0.40				
а	-	-	8°				
a1	-	-	7°				
All Dimensions in mm							

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	2.40
C1	0.95
G	1.60
Х	0.55
Υ	0.80
V1	3.20



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